

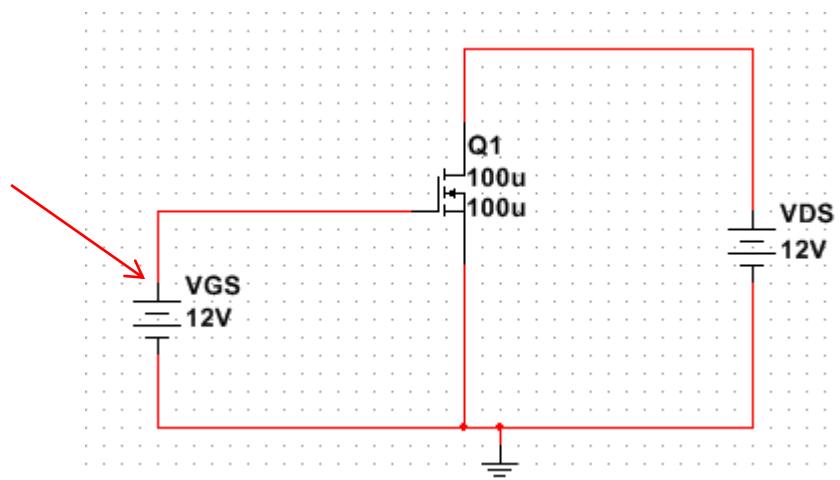
## EXPERIMENT TWO

### I/V characteristics of Enhancement MOSFET

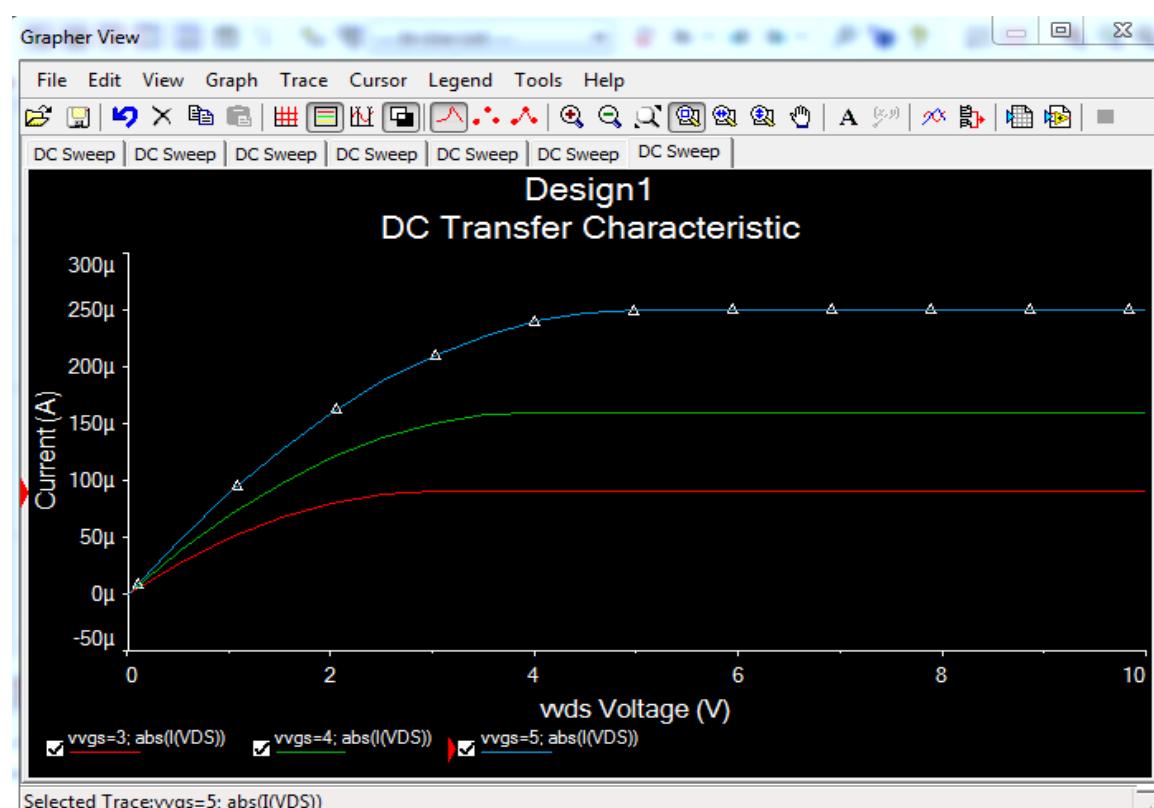
**AIM:** Study the relationship between drain current (**ID**) and gate source voltage (**VGS**).

**APPARATUS:** Enhancement MOSFET (Virtual transistor), breadboard, 2 D.C power supply and Ground.

#### Circuit Diagram:



#### Output:



## Procedure:

